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				Application Number	10/582,035-Conf. #1665			
II.	NFORMATION	l DI	SCLOSURE	Filing Date	May 7, 2007			
s	TATEMENT E	3Y /	APPLICANT	First Named Inventor	Shen			
				Art Unit	4146			
	(Use as many she	ets as	necessary)	Examiner Name	R. T. Huber			
Sheet	1	of	1	Attorney Docket Number	GWS-009			

			U.S.	PATE	NT DO	CUMENTS				
Examiner Initials*	Cite No.1	Document Number Number-Kind Code ² (of known)	Publication I MM-DD-YY		Name of Patentee or Applicant of Cited Document Shen et al.		Pages, Columns, Lines, Who Relevant Passages or Releva Figures Appear		here want	
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Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, senial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where publisher								T2
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	C9	Pavier et al., "Bi-directional FlipFET™ MOSFETs for Cell Phone Battery Protection Circuits," PCIM 2001.								
Examine							Date Considered			

^{*}EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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